

ECD - II
Electronic Circuit Analysis & Design - II

QP Code : NP-19767

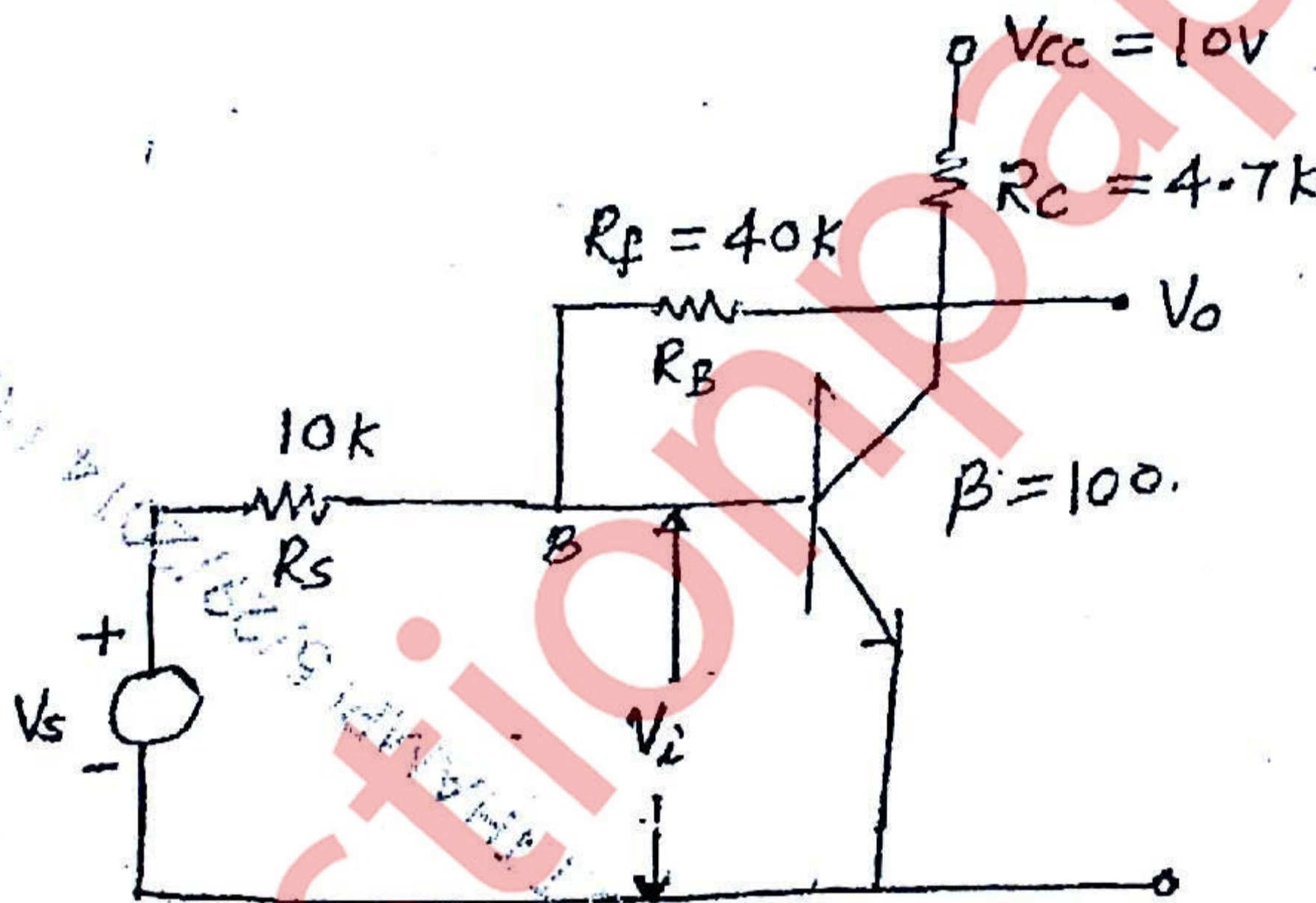
(3 Hours)

20

[Total Marks : 80

- N.B. : (1) Question No. 1 is compulsory.
(2) Answer any three questions from remaining five questions.
(3) Assume suitable data if necessary.

1. (a) Explain any two electrical characteristics of op-amp. Give its ideal and practical values. 5
- (b) Explain the advantages and limitations of use of swamping resistor in differential amplifier. 5
- (c) Distinguish Class B and Class C power amplifier. 5
- (d) Explain zero crossing detector. 5
2. (a) Compare various types of negative feedback. (Block diagram compulsory). 10
- (b) For the circuit shown in figure identify the feedback topology. Using negative feedback approach, determine A_{vf} , R_{if} and R_{of} . 10



3. (a) Derive expressions for input resistance, output resistance and voltage gain, CMRR for single input balanced output differential amplifier. 10
- (b) For the following given specifications for the dual input balanced output differential amplifier, 10

$$R_C = 2.2 \text{ K}, R_1 = 4.7 \text{ K}, R_{in1} = R_{in2} = 50 \Omega,$$

$$R_E = 1 \text{ K}, V_{CC} = 20 \text{ V}, V_{EE} = -20 \text{ V},$$

$$\beta_{dc} = \beta_{ac} = 100, V_{BE} = 0.7 \text{ V}.$$

Determine the quiescent collector current, collector to emitter voltage V_{CEQ} . Also calculate A_d , A_c , CMRR, R_{in} and R_o .

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4. (a) Derive expressions for maximum efficiency of transformer coupled class A amplifiers and also for class B amplifier. 10
- (b) Design class A transformer coupled amplifier to provide 12 W power to the speaker of 10 Ω . 10
5. (a) Derive a relation for frequency of oscillations and condition for sustained oscillations of wein Bridge Oscillator. 10
- (b) Design following circuits using op-amp :- 10
- (i) A sine wave of 1 KHz frequency.
- (ii) $V_o = - \int V_{in} \cdot dt$ 20
6. Explain following applications of op-amp (any two) :-
- (a) Temperature compensated log amplifier.
- (b) Instrumentation amplifier.
- (c) Precision rectifier.

DBEC DATA SHEET

Transistor type	P _{dmax} @ 25°C Watts	I _{cmax} @ 25°C Amps	V _{ce} d.c.	V _{ce} d.c.	V _{ce} d.c.	V _{ce} d.c.	V _{ce} d.c.	V _{ce} d.c.	V _{ce} d.c.	T _j max °C	D.C. current gain		h _{fe} max.	V _{ce} max.		
											min.	typ.			min.	typ.
2N3055	115.5	15.0	1.1	100	60	70	90	7	200	20	50	70	15	50	120	1.8
ECM055	50.0	5.0	1.0	60	50	55	60	5	200	25	50	100	25	75	125	1.5
ECM149	30.0	4.0	1.0	50	40	—	—	8	150	30	50	110	33	60	115	1.2
ECM100	5.0	0.7	0.6	70	60	65	—	6	200	50	90	280	50	90	280	0.9
BC147A	0.25	0.1	0.25	50	45	50	—	6	125	115	180	220	125	220	260	0.9
2N525(PNP)	0.225	0.5	0.25	85	30	—	—	—	100	35	—	65	—	45	—	—
BC147B	0.25	0.1	0.25	50	45	50	—	6	125	200	290	450	240	330	500	0.9

BFW 11—JFET MUTUAL CHARACTERISTICS

Transistor type	h _{ie}	h _{oe}	h _{re}	o _{ja}
BC 147A	2.7 K Ω	18 μ U	1.5 × 10 ⁻⁴	0.4°C/mw
2N 525 (PNP)	1.4 K Ω	25 μ U	3.2 × 10 ⁻⁴	—
BC 147B	4.5 K Ω	30 μ U	2 × 10 ⁻⁴	0.4°C/mw

N-Channel JFET

Type	V _{gs} max. Volts	V _{gs} max. Volts	V _{gs} max. Volts	P _d max. @25°C	I _{oss}	g _{ms}	-V _p Volts	r _d	Derate above 25°C
2N3822	50	50	50	300 mW	2 mA	3000 μΩ	6	50 KΩ	2 mW/°C
BFW 11 (typical)	30	30	30	300 mW	7 mA	5000 μΩ	2.5	50 KΩ	—

UJT type	P _d max. @25°C	I _e max. @25°C	peak pulse current	V _{base} Volts max.	T _j max	η	R _{th} KΩ	I _r
	300mW	50mA	2Amp.	30	125°C	0.50	4.7	9.1
2N2645	300mW	50mA	2Amp.	35	125°C	0.50	4.7	9.1